

| | Time Stamp | Comments | Error Definition | Errors |
|----|---------------------|----------|------------------|--------|
| 31 | 2002/12/12 17:08 | | | 0 |
| 32 | 2002/12/12 17:17 | | | 0 |
| 33 | 2002/12/12 17:21 | | | 0 |
| 34 | 2002/12/12 17:24 | | | 0 |
| 35 | 2002/12/12 17:25 | | | 0 |
| 36 | 2002/12/13 12:39 | | | 0 |
| 37 | 2002/12/13 11:28 | | | 0 |
| 38 | 2002/12/13 12:41 | | | 0 |
| 39 | 2002/12/13 12:41 | | | 0 |
| 40 | 2002/12/13 12:41 | | | 0 |
| 41 | 2002/12/13 12:41 | | | 0 |

| | Type | Hits | Search Text | DBs |
|----|------|------|--|---|
| 1 | BRS | 2 | WO-9639713-\$.did. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 2 | BRS | 2 | JP-06302813-\$.did. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 3 | BRS | 2 | 6417546.pn. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 4 | BRS | 2 | 6093661.pn. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 5 | BRS | 3 | 6093661.URPN. | USPAT |
| 6 | BRS | 0 | 6417546.URPN. | USPAT |
| 7 | BRS | 16 | ("4651406" "5254489" "5464792" "5502009" "5596218" "5620908" "5674788" "5716864" "5960302" "5972783" "5994749" "6136654" "6153538" "6165846" "6200834" "6225151").PN. | USPAT |
| 8 | BRS | 5 | ("5254489" "5464792" "5620908" "5716864" "5972783").PN. | USPAT |
| 9 | BRS | 388 | 438/199.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 10 | BRS | 487 | 438/207.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 11 | BRS | 104 | 438/288.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 12 | BRS | 444 | 438/296.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 13 | BRS | 78 | 438/513.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 14 | BRS | 124 | 438/769.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 15 | BRS | 1 | (cmos near3 transistor) and (substrate same (silicon adj dioxide) same plasma same nitrogen same (silicon adj nitride)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 16 | BRS | 137 | (transistor) and (substrate same (silicon adj dioxide) same nitrogen same (silicon adj nitride)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |

| | Time Stamp | Comments | Error Definition | Errors |
|----|---------------------|----------|------------------|--------|
| 1 | 2002/09/17 16:33 | | | 0 |
| 2 | 2002/09/17 16:33 | | | 0 |
| 3 | 2002/11/05 15:24 | | | 0 |
| 4 | 2002/11/05 15:26 | | | 0 |
| 5 | 2002/11/05 15:27 | | | 0 |
| 6 | 2002/11/05 15:27 | | | 0 |
| 7 | 2002/11/05 15:28 | | | 0 |
| 8 | 2002/11/05 15:29 | | | 0 |
| 9 | 2002/11/05 17:09 | | | 0 |
| 10 | 2002/11/05 17:09 | | | 0 |
| 11 | 2002/11/05 17:09 | | | 0 |
| 12 | 2002/11/05 17:09 | | | 0 |
| 13 | 2002/11/05 17:10 | | | 0 |
| 14 | 2002/11/05 17:10 | | | 0 |
| 15 | 2002/11/05 17:15 | | | 0 |
| 16 | 2002/11/05 17:20 | | | 0 |

| | Type | Hits | Search Text | DBs |
|----|------|------|---|---|
| 17 | BRS | 1 | (transistor) and (substrate same (gate adj oxide with silicon adj dioxide) same nitrogen same (silicon adj nitride)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 18 | BRS | 73 | (transistor) and (substrate same (gate adj oxide) same nitrogen same (silicon adj nitride)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 19 | BRS | 155 | 438/775.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 20 | BRS | 22 | 438/775.ccls. and activat\$3 and plasma | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 21 | BRS | 13 | 438/775.ccls. and (plasma with power) and anneal\$3 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 22 | BRS | 20 | 438/775.ccls. and (plasma with power) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 23 | BRS | 1 | 438/775.ccls. and (anneal\$3 same temperature same time same (rapid adj thermal adj process\$3) same rate) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 24 | BRS | 1 | 438/775.ccls. and (anneal\$3 same temperature same time same (rapid adj thermal adj process\$3) same ramp) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 25 | BRS | 2 | 438/775.ccls. and (anneal\$3 same temperature same time same (rapid adj thermal adj process\$3 or RTP) same rate) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 26 | BRS | 26 | transistor and (nitrogen or nitride) and (anneal\$3 same temperature same time same (rapid adj thermal adj process\$3 or RTP) same rate) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 27 | BRS | 8 | transistor and (nitrogen or nitride) same (anneal\$3 same temperature same time same (rapid adj thermal adj process\$3 or RTP) same rate) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 28 | BRS | 6 | transistor and (nitrogen or nitride) same (anneal\$3 same temperature same time same (rapid adj thermal adj process\$3 or RTP) same (ramp\$3 adj rate)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 29 | BRS | 2 | 438/775.ccls. and activat\$3 same (surface near3 temperature) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 30 | BRS | 7 | 438/775.ccls. and activat\$3 and (surface near3 temperature) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |

| | Time Stamp | Comments | Error Definition | Errors |
|----|---------------------|----------|------------------|--------|
| 17 | 2002/12/12 17:06 | | | 0 |
| 18 | 2002/11/05 17:28 | | | 0 |
| 19 | 2002/11/05 17:43 | | | 0 |
| 20 | 2002/11/05 18:16 | | | 0 |
| 21 | 2002/11/05 17:55 | | | 0 |
| 22 | 2002/11/05 18:04 | | | 0 |
| 23 | 2002/11/05 18:06 | | | 0 |
| 24 | 2002/11/05 18:06 | | | 0 |
| 25 | 2002/11/05 18:10 | | | 0 |
| 26 | 2002/11/05 18:11 | | | 0 |
| 27 | 2002/11/05 18:12 | | | 0 |
| 28 | 2002/11/05 18:13 | | | 0 |
| 29 | 2002/11/05 18:18 | | | 0 |
| 30 | 2002/11/05 18:17 | | | 0 |

| | Type | Hits | Search Text | DBs |
|----|------|------|---|---|
| 31 | BRS | 141 | (transistor) and (substrate same (silicon adj dioxide) same nitrogen same (silicon adj nitride)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 32 | BRS | 6 | (transistor) and (substrate same (silicon adj dioxide) same nitrogen same (silicon adj nitride)) and ((nitride or nitrogen) with atom\$2 with (percent or "%")) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 33 | BRS | 3 | (transistor) and (substrate same (gate adj oxide) same nitrogen same (silicon adj nitride)) and ((nitride or nitrogen) with atom\$2 with (percent or "%")) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 34 | BRS | 44 | (transistor) and (substrate same nitrogen same (silicon adj nitride)) and ((nitride or nitrogen) with atom\$2 with (percent or "%")) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 35 | BRS | 42 | (transistor) and (substrate same nitrogen with (implant\$5 or diffus\$3)) and ((nitride or nitrogen) with atom\$2 with (percent or "%")) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 36 | BRS | 1268 | (transistor) and (substrate same nitrogen with (implant\$5 or diffus\$3)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 37 | BRS | 7 | ("5254489" "5716863" "5763922" "5989962" "6048769" "6093661" "6171911").PN. | USPAT |
| 38 | BRS | 71 | (transistor) and (substrate same nitrogen with activat\$3 same temperature) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 39 | BRS | 168 | (transistor) and (nitrogen with activat\$3 same temperature) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 40 | BRS | 68 | (transistor) and (nitrogen with activat\$3 with temperature) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 41 | BRS | 17 | (transistor) and (substrate same nitrogen with activat\$3 with temperature) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |